

25TTS...FPPbF High Voltage Series



Vishay High Power Products Phase Control SCR
TO-220AB FULL-PAK, 25 A

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS
			TYP.	MAX.	
Maximum average on-state current	$I_{T(AV)}$	$T_C = 85^\circ\text{C}$, 180° conduction half sine wave	16		A
Maximum RMS on-state current	I_{RMS}		25		
Maximum peak, one-cycle, non-repetitive surge current	I_{TSM}	10 ms sine pulse, rated V_{RRM} applied	300		
		10 ms sine pulse, no voltage reapplied	350		
Maximum I^2t for fusing	I^2t	10 ms sine pulse, rated V_{RRM} applied	450		A^2s
		10 ms sine pulse, no voltage reapplied	630		
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	$t = 0.1$ to 10 ms, no voltage reapplied	6300		$A^2\sqrt{s}$
Maximum on-state voltage drop	V_{TM}	16 A, $T_J = 25^\circ\text{C}$	1.25		V
On-state slope resistance	r_t	$T_J = 125^\circ\text{C}$	12.0		$m\Omega$
Threshold voltage	$V_{T(TO)}$		1.0		V
Maximum reverse and direct leakage current	I_{RM}/I_{DM}	$T_J = 25^\circ\text{C}$	0.5		mA
		$T_J = 125^\circ\text{C}$	10		
Holding current	I_H	Anode supply = 6 V, resistive load, initial $I_T = 1$ A	-	100	
Maximum latching current	I_L	Anode supply = 6 V, resistive load	200		
Maximum rate of rise of off-state voltage	dV/dt		500		V/ μs
Maximum rate of rise of turned-on current	dI/dt		150		A/ μs

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P_{GM}		8.0	W
Maximum average gate power	$P_{G(AV)}$		2.0	
Maximum peak positive gate current	$+I_{GM}$		1.5	A
Maximum peak negative gate voltage	$-V_{GM}$		10	V
Maximum required DC gate current to trigger	I_{GT}	Anode supply = 6 V, resistive load, $T_J = -10^\circ\text{C}$	60	mA
		Anode supply = 6 V, resistive load, $T_J = 25^\circ\text{C}$	45	
		Anode supply = 6 V, resistive load, $T_J = 125^\circ\text{C}$	20	
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, $T_J = -10^\circ\text{C}$	2.5	V
		Anode supply = 6 V, resistive load, $T_J = 25^\circ\text{C}$	2.0	
		Anode supply = 6 V, resistive load, $T_J = 125^\circ\text{C}$	1.0	
Maximum DC gate voltage not to trigger	V_{GD}	$T_J = 125^\circ\text{C}$, $V_{DRM} = \text{Rated value}$	0.25	mA
Maximum DC gate current not to trigger	I_{GD}		2.0	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t_{gt}	$T_J = 25^\circ\text{C}$	0.9	μs
Typical reverse recovery time	t_{rr}	$T_J = 125^\circ\text{C}$	4	
Typical turn-off time	t_q		110	



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THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		- 40 to 125	°C
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.5	°C/W
Maximum thermal resistance, junction to ambient	R _{thJA}		62	
Typical thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth and greased	1.5	
Approximate weight			2	g
			0.07	oz.
Mounting torque	minimum		6 (5)	kgf · cm (lbf · in)
	maximum		12 (10)	
Marking device		Case style TO-220AB FULL-PAK (94/V0)	25TTS08FP	
			25TTS12FP	

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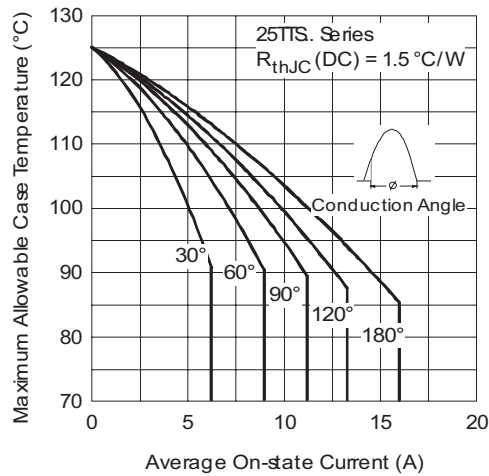


Fig. 1 - Current Rating Characteristics

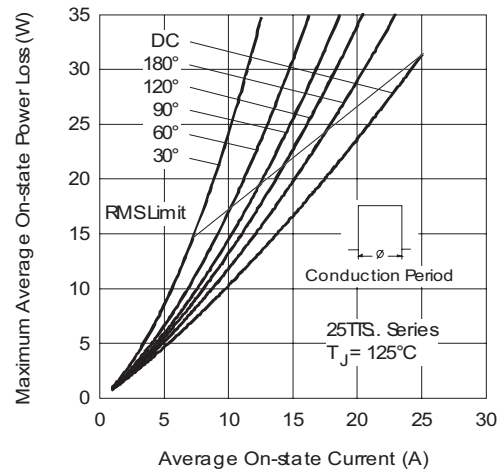


Fig. 4 - On-State Power Loss Characteristics

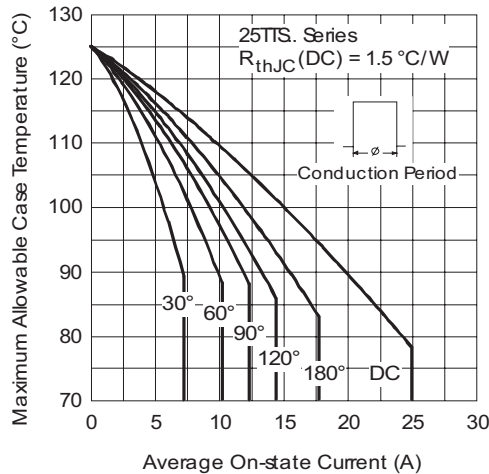


Fig. 2 - Current Rating Characteristics

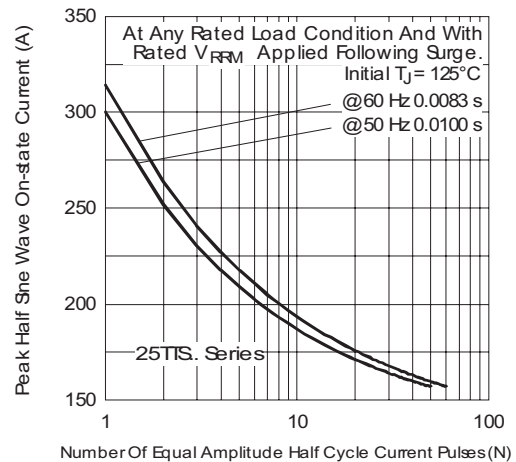


Fig. 5 - Maximum Non-Repetitive Surge Current

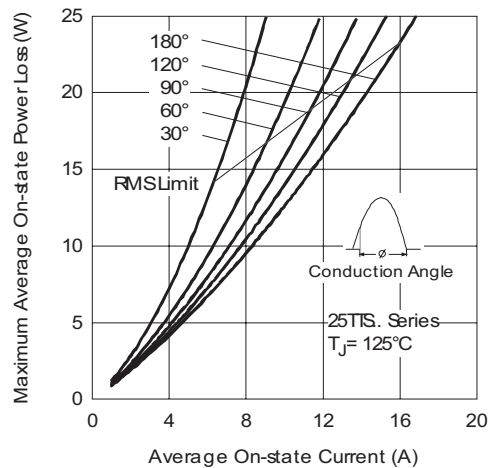


Fig. 3 - On-State Power Loss Characteristics

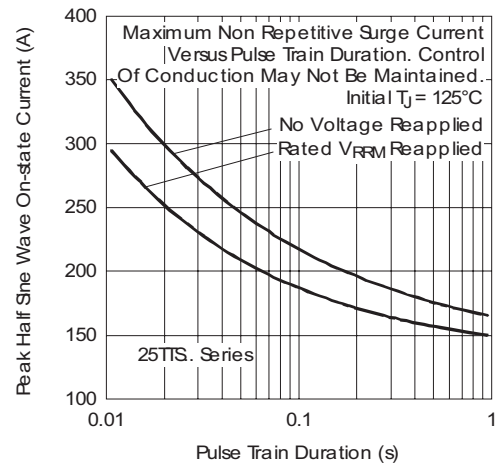


Fig. 6 - Maximum Non-Repetitive Surge Current



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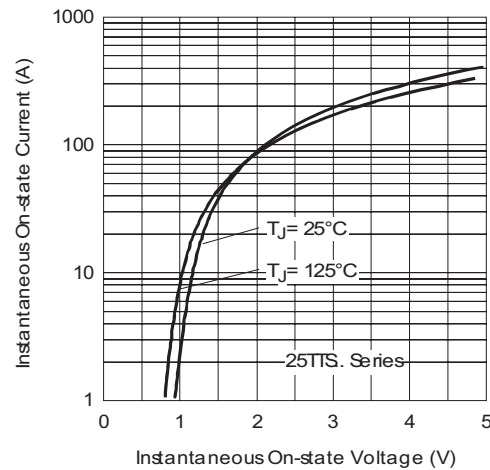


Fig. 7 - On-State Voltage Drop Characteristics

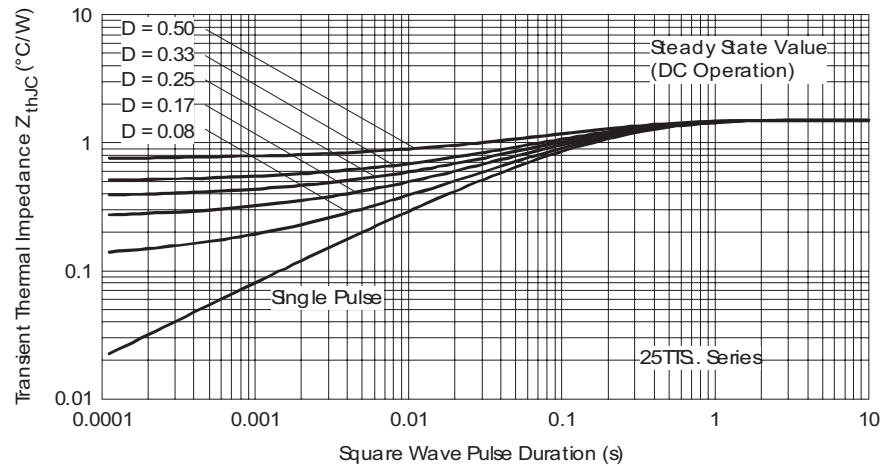


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

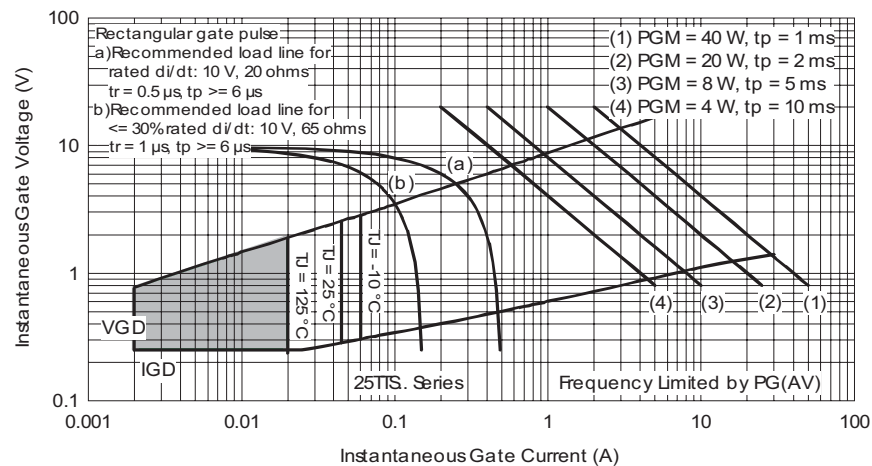


Fig. 9 - Gate Characteristics

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ORDERING INFORMATION TABLE

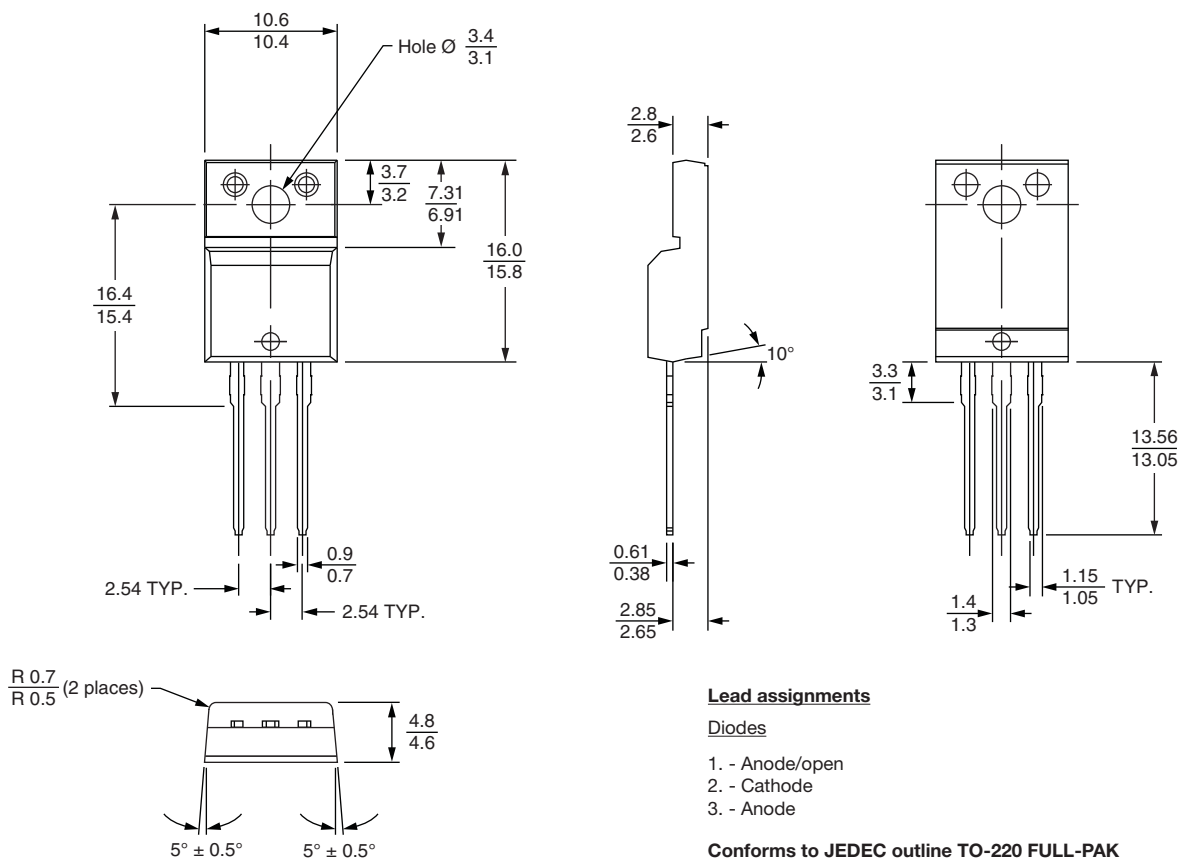
Device code	25	T	T	S	12	FP	PbF
	1	2	3	4	5	6	7
1	- Current rating (25 = 25 A)						
2	- Circuit configuration: T = Single thyristor						
3	- Package: T = TO-220AB						
4	- Type of silicon: Standard recovery rectifier						
5	- Voltage code x 100 = V_{RRM}						
6	- FULL-PAK						
7	• None = Standard production • PbF = Lead (Pb)-free						

08 = 800 V
12 = 1200 V

LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95072
Part marking information	http://www.vishay.com/doc?95069



DIMENSIONS in millimeters



Lead assignments

Diodes

1. - Anode/open
2. - Cathode
3. - Anode

Conforms to JEDEC outline TO-220 FULL-PAK



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